



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



Reflective photosensor (photoreflector)

RPR-359F

The RPR-359F is a reflective photosensor. The emitter is a GaAs infrared light emitting diode and the detector is a high-sensitivity, silicon planar phototransistor. A plastic lens is used for high sensitivity. In addition, since it is molded in plastic with a visible light filter, there is almost no effect from stray light.

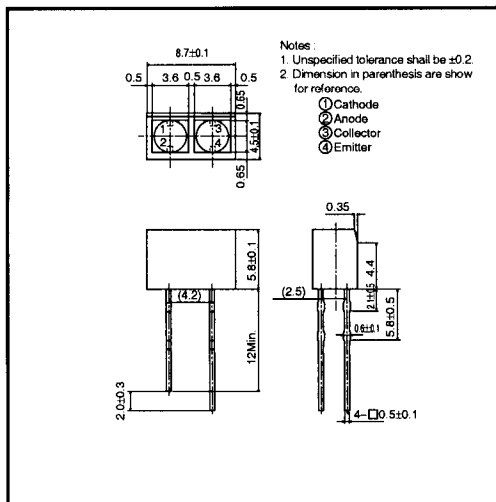
●Application

Copiers, Compact disc players

●Features

- 1) A plastic lens is used for high sensitivity.
- 2) A built-in visible light filter minimizes the influence of stray light.
- 3) Low collector-emitter saturation voltage.
- 4) Lightweight and compact.

●External dimensions (Units : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Input (LED)	Forward current	I_F	50	mA
	Reverse voltage	V_R	5	V
	Power dissipation	P_D	80	mW
Output (Photo-transistor)	Collector-emitter voltage	V_{CE0}	30	V
	Emitter-collector voltage	V_{ECO}	4.5	V
	Collector current	I_C	30	mA
	Collector power dissipation	P_C	100	mW
Operating temperature		T_{opr}	-25~+85	°C
Storage temperature		T_{stg}	-40~+100	°C

Sensors

●Electrical and optical characteristics (Ta=25°C)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Conditions
Input characteristics	Forward voltage	V_F	-	1.3	1.6	V	$I_F=50\text{mA}$
	Reverse current	I_R	-	-	10	μA	$V_R=5\text{V}$
Output characteristics	Dark current	I_{CE0}	-	-	0.5	μA	$V_{CE}=10\text{V}$
	Peak sensitivity wavelength	λ_P	-	800	-	nm	-
Transfer characteristics	Collector current	I_C^*	200	500	1800	μA	$V_{CC}=5\text{V}$, $I_F=20\text{mA}$, $R_L=100\Omega$, $d=3.5\text{mm}$
	Collector-emitter saturation voltage	$V_{CE(sat)}$	-	0.1	0.3	V	$I_F=20\text{mA}$, $I_C=100\mu\text{A}$
	Response time	$tr\text{-}tf$	-	10	-	μs	$V_{CC}=10\text{V}$, $I_F=20\text{mA}$, $R_L=100\Omega$

* Standard paper (90% reflection)

●Electrical and optical characteristic curves

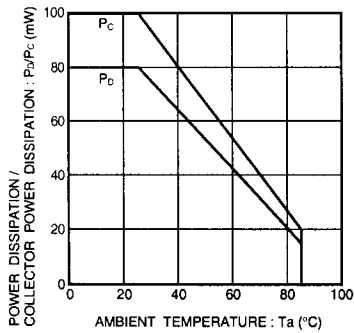


Fig.1 Power dissipation / collector power dissipation vs. ambient temperature

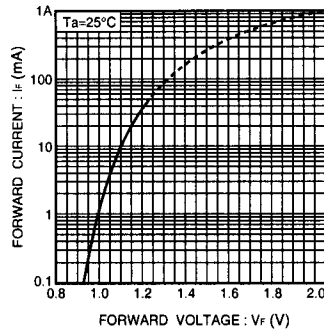


Fig.2 Forward current vs. forward voltage

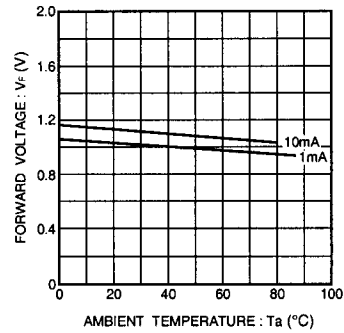


Fig.3 Forward voltage vs. ambient temperature

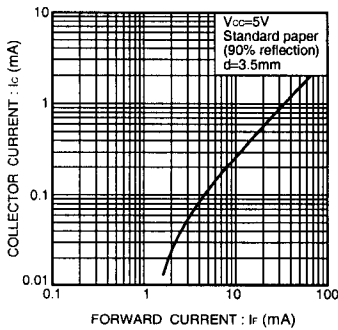


Fig.4 Collector current vs. forward current

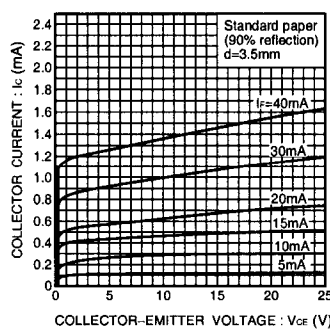


Fig.5 Output characteristics

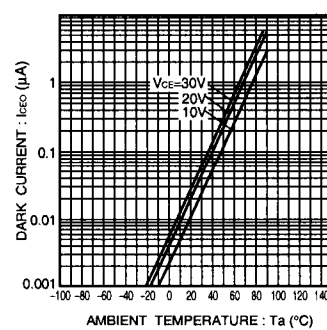


Fig.6 Dark current vs. ambient temperature